



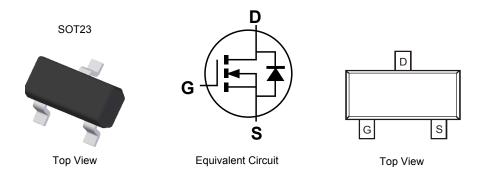
N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
MMBF170-7-F	SOT23	3000/Tape & Reel
MMBF170-13-F	SOT23	10000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant

 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





K6Z = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) $\overline{Y}M$ = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2014) M = Month (ex: 9 = September)

Chengdu A/T Site

Shanghai A/T Site

Date	Code	Kev	

Notes:

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Year	1998	1999	2000	2001	2002	2003	2004		2011	2012	2013	2014	2015	2016	2017
Code	J	К	L	М	Ν	Р	R		Y	Z	Α	В	С	D	E
Month	Jan	Fe	b I	Mar	Apr	Мау	Ju	n	Jul	Aug	Sep	Oc	t	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		Ν	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	60	V
Drain-Gate Voltage $R_{GS} \le 1.0M\Omega$		V _{DGR}	60	V
Gate-Source Voltage	Continuous Pulsed	V _{GSS}	±20 ±40	V
Drain Current (Note 5)	Continuous Pulsed	ID	500 800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	PD	300 1.80	m₩ m₩/°C
Thermal Resistance, Junction to Ambient	R _{0JA}	417	K/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

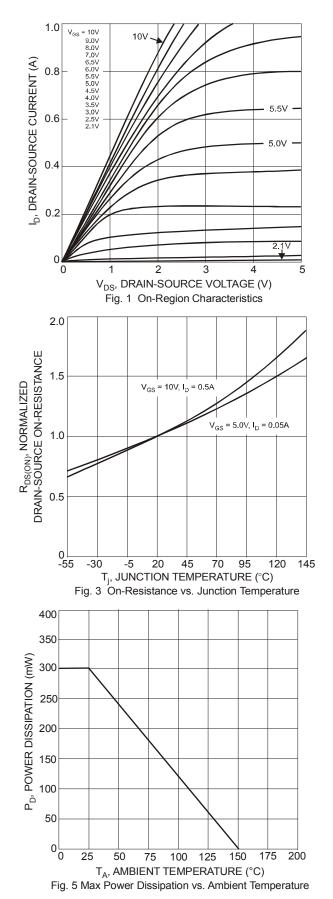
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						·
Drain-Source Breakdown Voltage	BV _{DSS}	60	70		V	V _{GS} = 0V, I _D = 100µA
Zero Gate Voltage Drain Current	I _{DSS}		_	1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage	I _{GSS}		_	±10	nA	V _{GS} = ±15V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)	•					·
Gate Threshold Voltage	V _{GS(th)}	0.8	2.1	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance	R _{DS} (ON)	_	_	5.0 5.3	Ω	V _{GS} = 10V, I _D = 200mA V _{GS} = 4.5V, I _D = 50mA
Forward Transconductance	g fs	80	_	_	mS	V _{DS} =10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS	•					•
Input Capacitance	Ciss		22	40	pF	
Output Capacitance	Coss		11	30	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		2.0	5.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Time	t _{on}		—	10	ns	V _{DD} = 25V, I _D = 0.5A,
Turn-Off Time	t _{off}		—	10	ns	V_{GS} = 10V, R_{GEN} = 50 Ω

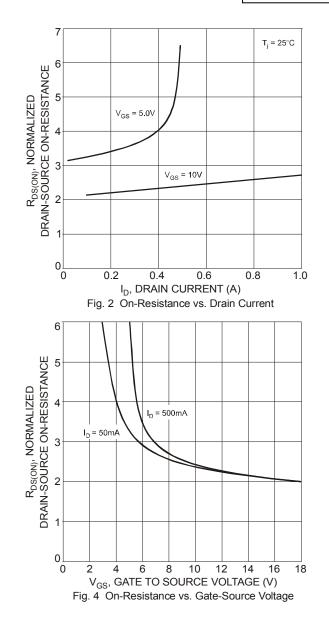
Notes: 5. Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com.

6. Short duration pulse test used to minimize self-heating effect.





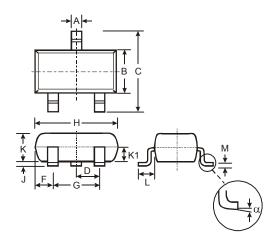






Package Outline Dimensions

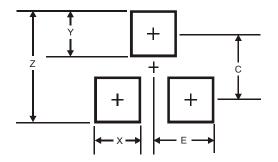
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
κ	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
М	0.085	0.18	0.11				
α	0°	8°	-				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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